

#### **Features**

- Split Gate Trench MOSFET Technology
- · Excellent Package for Heat Dissipation
- High Density Cell Design for Low R<sub>DS(on)</sub>
- Epoxy Meets UL 94 V-0 Flammability Rating
- · Moisture Sensitivity Level 1
- Halogen Free. "Green" Device (Note 1)
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

# **Maximum Ratings**

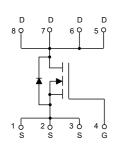
- Operating Junction Temperature Range: -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance: 20°C/W Junction to Ambient(Note 2)
- Thermal Resistance: 1.04°C/W Junction to Case

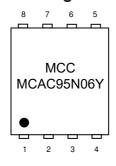
Parameter	Symbol	Rating	Unit	
Drain-Source Voltage		V <sub>DS</sub>	60	V
Gate-Source Volltage		V <sub>GS</sub>	±20	V
Continuous Drain Current <sup>(Note 3)</sup>	T <sub>C</sub> =25°C	_ I <sub>D</sub>	95	Α
	T <sub>C</sub> =100°C	_ 'D	60	Α
Pulsed Drain Current (Note 4)		I <sub>DM</sub>	390	Α
Avalanche Energy (Note 5)		E <sub>AS</sub>	500	mJ
Total Power Dissipation (Note 6)		P <sub>D</sub>	120	W

#### Note:

- 1. Halogen free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 2. The value of  $R_{\theta JA}$  is measured with the device mounted on 1 in  $^2$  FR-4 board with 2oz. copper, in a still air environment with  $T_A$ =25°C.
- 3. The maximum current rating is package limited.
- 4. Repetitive rating; pulse width limited by max. junction temperature.
- 5.  $V_{DD}$ =50V,  $R_G$ =25 $\Omega$ , L=0.5mH, starting  $T_J$ =25°C.
- 6. P<sub>D</sub> is based on max. junction temperature, using junction-case thermal resistance.

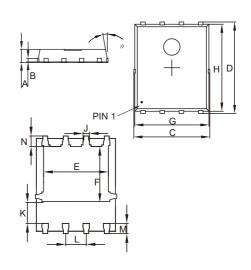
#### **Internal Structure and Marking Code**





# N-CHANNEL MOSFET

# **DFN5060**



DIMENSIONS					
DIM	INC	HES	MM		NOTE
DIIVI	MIN	MAX	MIN	MAX	NOIL
Α	0.031	0.047	0.80	1.20	
В	0.010		0.254		TYP.
С	0.193	0.222	4.90	5.64	
D	0.232	0.250	5.90	6.35	
Е	0.148	0.167	3.75	4.25	
F	0.126	0.154	3.20	3.92	
G	0.189	0.213	4.80	5.40	
Н	0.222	0.239	5.65	6.06	
K	0.045	0.059	1.15	1.50	
J	0.012	0.020	0.30	0.50	
L	0.046	0.054	1.17	1.37	
М	0.012	0.028	0.30	0.71	
N	0.016	0.028	0.40	0.71	

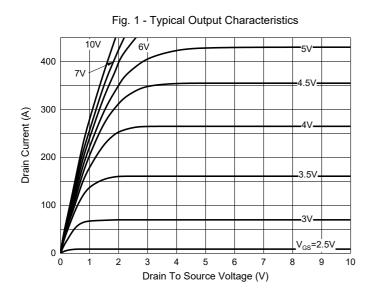


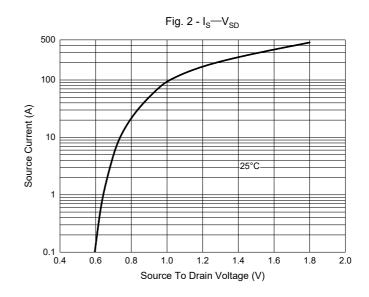
# Electrical Characteristics @ 25°C (Unless Otherwise Specified)

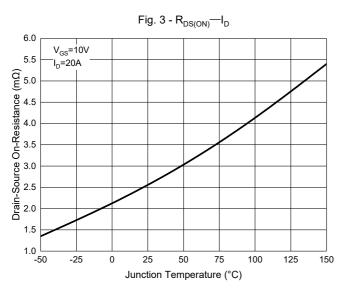
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static Characteristics					1		
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	60			V	
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> =±20V			±100	nA	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =60V, V <sub>GS</sub> =0V			1	μA	
Gate-Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS}=V_{GS}$ , $I_{D}=250\mu A$	1.2	1.8	2.2	V	
Drain-Source On-Resistance	_	V <sub>GS</sub> =10V, I <sub>D</sub> =20A		2.1	2.5	mΩ	
	$R_{DS(on)}$	V <sub>GS</sub> =4.5V, I <sub>D</sub> =15A		2.7	3.4	mΩ	
Diode Characteristics				•			
Continuous Body Diode Current	Is				95	Α	
Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =20A			1.2	V	
Reverse Recovery Time	t <sub>rr</sub>	L -054 di/dt-4004/		68		ns	
Reverse Recovery Charge	Q <sub>rr</sub>	I <sub>S</sub> =25A,di/dt=100A/μs		73		nC	
Dynamic Characteristics				•			
Input Capacitance	C <sub>iss</sub>			5950			
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> =25V,V <sub>GS</sub> =0V,f=100KHz		1250		pF	
Reverse Transfer Capacitance	C <sub>rss</sub>			85			
Total Gate Charge	Qg			93			
Gate-Source Charge	Q <sub>gs</sub>	V <sub>DS</sub> =50V,V <sub>GS</sub> =10V,I <sub>D</sub> =50A		17		nC	
Gate-Drain Charge	$Q_{gd}$			14			
Turn-On Delay Time	t <sub>d(on)</sub>			22.5			
Turn-On Rise Time	t <sub>r</sub>	V <sub>GS</sub> =10V,V <sub>DD</sub> =30V, I <sub>D</sub> =25A,		6.7		<b></b>	
Turn-Off Delay Time	t <sub>d(off)</sub>	R <sub>GEN</sub> =2Ω		80.3		ns	
Turn-Off Fall Time	t <sub>f</sub>			26.9			

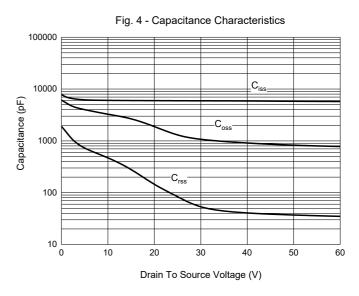


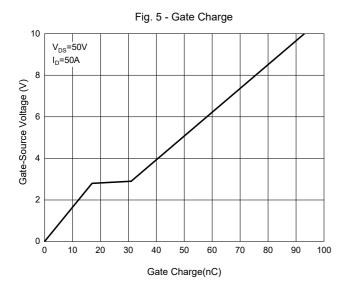
#### **Curve Characteristics**

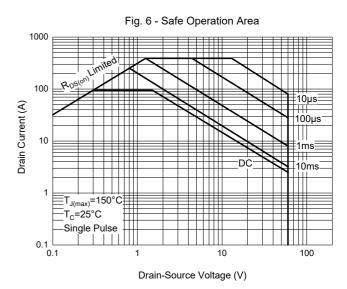






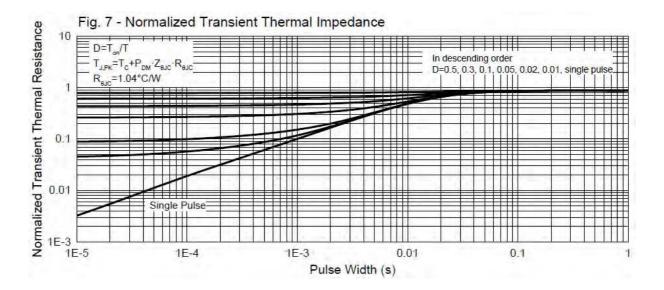








## **Curve Characteristics**





## **Ordering Information**

Device	Packing	
Part Number-TP	Tape&Reel: 5Kpcs/Reel	

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